

/ Descriptions

KF \$0) E GE Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

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High gain, good linearity of h_{FE} .

/ Applications

TV final picture IF amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Collector PIN 2 Emitter PIN 3 Base

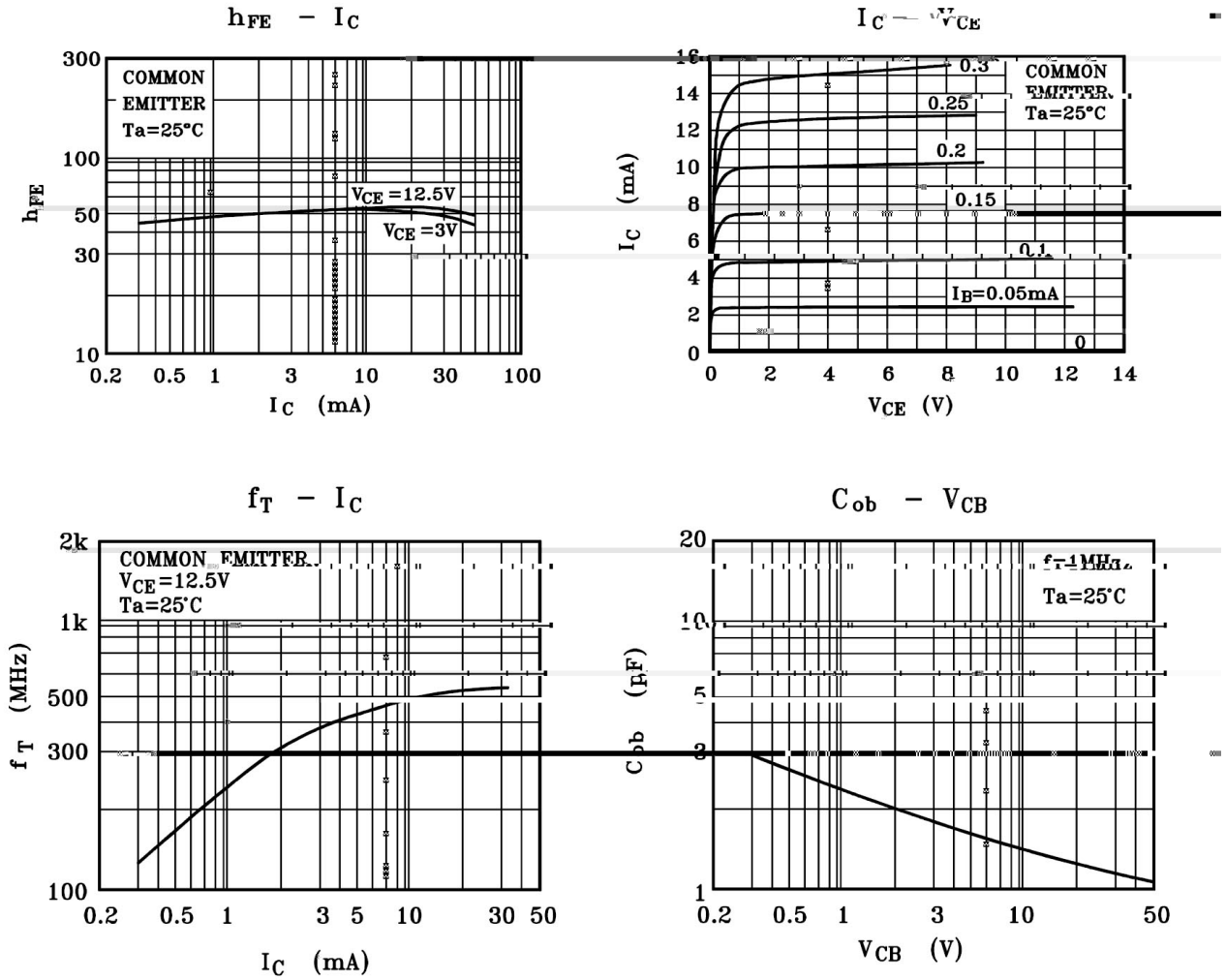
/ hFE Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	50	mA
Emitter Current - Continuous	I_E	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	25			V

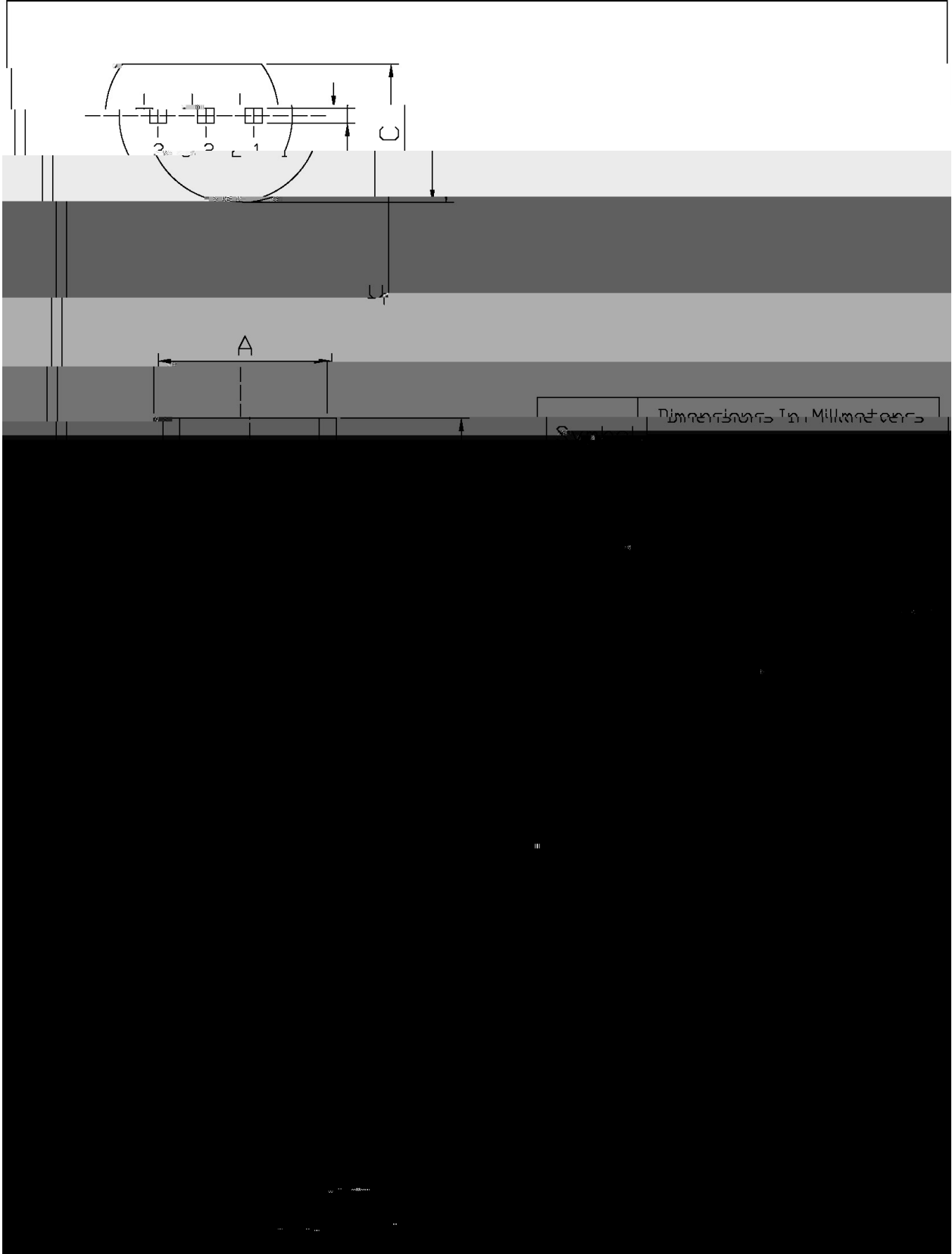
/ Electrical Characteristic Curve



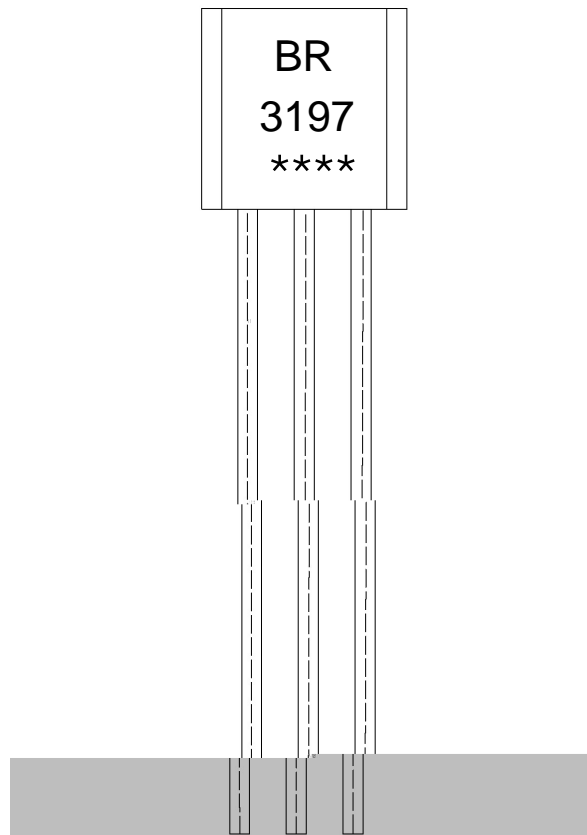
/ Package Dimensions

TO-92

Unit: mm



/ Marking Instructions



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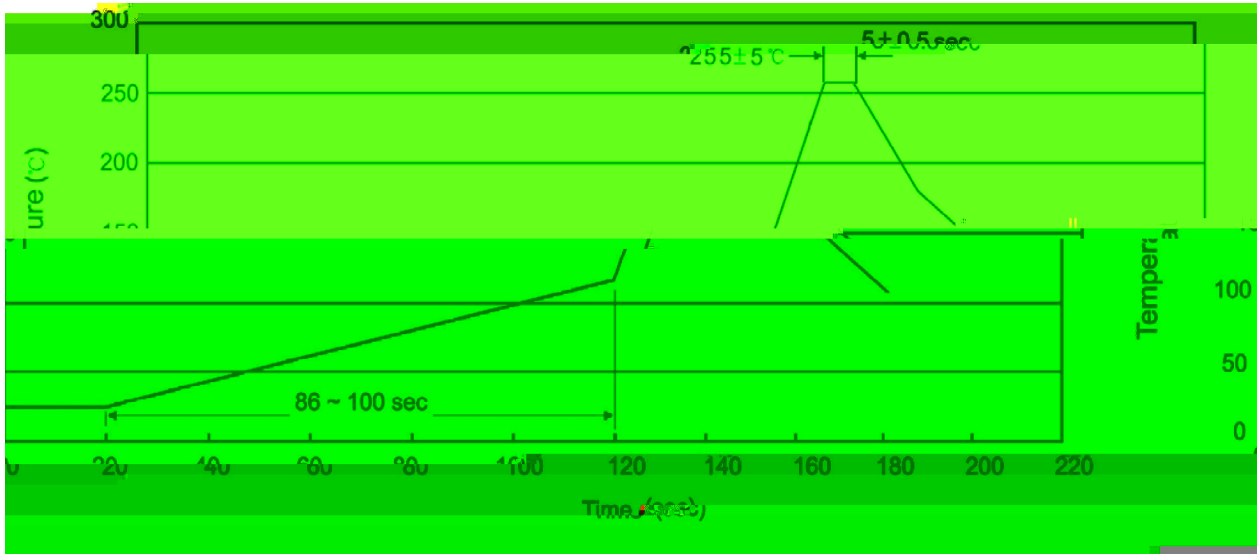
Note:

BR: Company Code.

3197: Product Type.

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|-----|------------|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | | 5..0.5sec; | | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270..5 10..1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK